

Data Sheet September 2004 FN3123.4

· Pb-free Available as an Option

# High Speed, Quad SPST, CMOS Analog Switch

The HI-201HS is a monolithic CMOS Analog Switch featuring very fast switching speeds and low ON resistance. The integrated circuit consists of four independently selectable SPST switches and is pin compatible with the industry standard HI-201 switch.

Fabricated using silicon-gate technology and the Intersil Dielectric Isolation process, this TTL compatible device offers improved performance over previously available CMOS analog switches. Featuring maximum switching times of 50ns, low ON resistance of  $50\Omega$  maximum, and a wide analog signal range, the HI-201HS is designed for any application where improved switching performance, particularly switching speed, is required. (A more detailed discussion on the design and application of the HI-201HS can be found in Application Note AN543.)

# **Ordering Information**

		I	
PART NUMBER	TEMP. RANGE (°C)	PACKAGE	PKG. DWG.#
HI1-0201HS-2	-55 to 125	16 Ld CERDIP	F16.3
HI1-0201HS-4	-25 to 85	16 Ld CERDIP	F16.3
HI1-0201HS-5	0 to 75	16 Ld CERDIP	F16.3
HI3-0201HS-5	0 to 75	16 Ld PDIP	E16.3
HI3-0201HS-5Z (See Note)	0 to 75	16 Ld PDIP (Pb-free)	E16.3
HI9P0201HS-5	0 to 75	16 Ld SOIC	M16.3
HI9P0201HS-5Z (See Note)	0 to 75	16 Ld SOIC (Pb-free)	M16.3
HI9P0201HS-9	-40 to 85	16 Ld SOIC	M16.3
HI9P0201HS-9Z (See Note)	-40 to 85	16 Ld SOIC (Pb-free)	M16.3

NOTE: Intersil Pb-free products employ special Pb-free material sets; molding compounds/die attach materials and 100% matte tin plate termination finish, which is compatible with both SnPb and Pb-free soldering operations. Intersil Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020C.

#### **Features**

· · · · · · · · · · · · · · · · · · ·
Fast Switching Times
- t <sub>ON</sub>
- t <sub>OFF</sub> 40ns
• Low "ON" Resistance
Pin Compatible with Standard HI-201
• Wide Analog Voltage Range (±15V Supplies) ±15V
• Low Charge Injection (±15V Supplies) 10pC

#### TTL Compatible

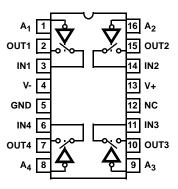
• Symmetrical Switching Analog Current Range . . . . . 80mA

# **Applications**

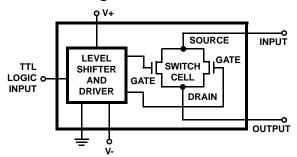
- · High Speed Multiplexing
- · High Frequency Analog Switching
- · Sample and Hold Circuits
- · Digital Filters
- · Operational Amplifier Gain Switching Networks
- · Integrator Reset Circuits

**Pinout** (Switches Shown For Logic "1" Input)

HI-201HS (CERDIP, PDIP, SOIC)
TOP VIEW



# Functional Diagram

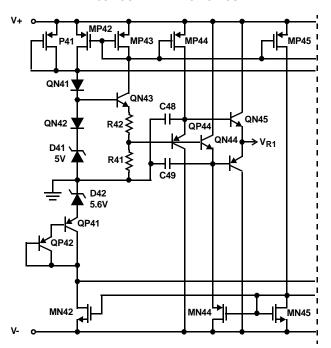


**TRUTH TABLE** 

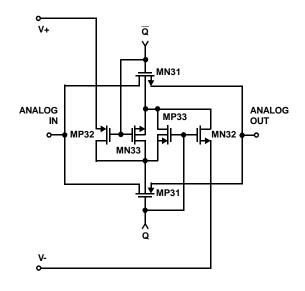
LOGIC	SWITCH
0	ON
1	OFF

# Schematic Diagrams



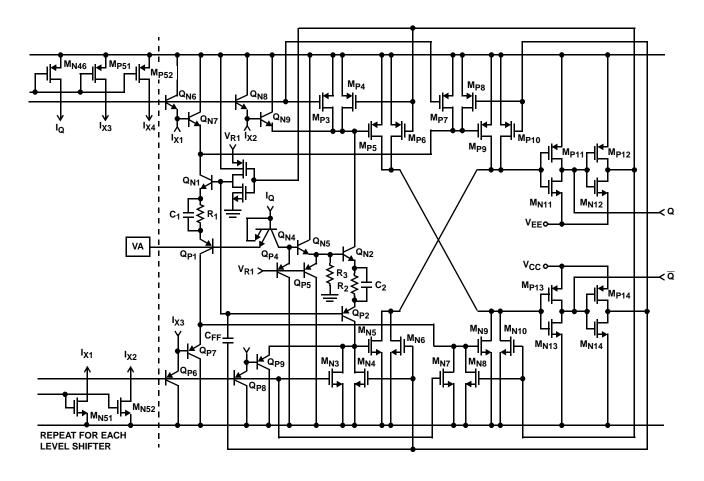


#### **SWITCH CELL**



# Schematic Diagrams (Continued)

#### DIGITAL INPUT BUFFER AND LEVEL SHIFTER



#### **Absolute Maximum Ratings**

#### **Operating Conditions**

Temperature Ranges	
HI-201HS-2	55°C to 125°C
HI-201HS-4	25°C to 85°C
=== =	0°C to 75°C
HI-201HS-9	40 <sup>o</sup> C to 85 <sup>o</sup> C

#### **Thermal Information**

Thermal Resistance (Typical, Note 1)	$\theta_{JA}$ (oC/W)	θ <sub>JC</sub> (oC/M)
CERDIP Package	80	20
PDIP Package	90	N/A
SOIC Package	100	N/A
Maximum Junction Temperature		
Ceramic Package		
Plastic Package		150 <sup>o</sup> C
Maximum Storage Temperature	65	<sup>o</sup> C to 150°C
Maximum Lead Temperature (Soldering 1 (SOIC - Lead Tips Only)	0s)	300°C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

#### NOTE:

1.  $\theta_{\mbox{\scriptsize JA}}$  is measured with the component mounted on an evaluation PC board in free air.

**Electrical Specifications** Supplies = +15V, -15V;  $V_{AH}$  (Logic Level High) = 2.4V,  $V_{AL}$  (Logic Level Low) = +0.8V, GND = 0V, Unless Otherwise Specified

PARAMETER	TEST CONDITIONS	TEMP (°C)		-2			-4, -5, -9		
			MIN	TYP	MAX	MIN	TYP	MAX	UNITS
DYNAMIC CHARACTERISTICS		l	<u>I</u>	U.		U.	U.	l	
Switch ON Time, t <sub>ON</sub>	(Note 3)	25	-	30	50	-	30	50	ns
Switch OFF Time, t <sub>OFF1</sub>	(Note 3)	25	-	40	50	-	40	50	ns
Switch OFF Time, t <sub>OFF2</sub>	(Note 3)	25	-	150	-	-	150	-	ns
Output Settling Time	To 0.1%	25	-	180	-	-	180	-	ns
Charge Injection, Q	(Note 6)	25	-	10	-	-	10	-	pC
OFF Isolation	(Note 4)	25	-	72	-	-	72	-	dB
Crosstalk	(Note 5)	25	-	86	-	-	86	-	dB
Input Switch Capacitance, C <sub>S(OFF)</sub>		25	-	10	-	-	10	-	pF
Output Switch Capacitance C <sub>D(OFF)</sub>		25	-	10	-	-	10	-	pF
C <sub>D(ON)</sub>		25	-	30	-	-	30	-	pF
Digital Input Capacitance, CA		25	-	18	-	-	18	-	pF
Drain-To-Source Capacitance, C <sub>DS(OFF)</sub>		25	-	0.5	-	-	0.5	-	pF
DIGITAL INPUT CHARACTERISTICS	1	ļ.	1					l	-
Input Low Threshold, V <sub>AL</sub>		Full	-	-	0.8	-	-	0.8	V
Input High Threshold, V <sub>AH</sub>		25	2.0	-	-	2.0	-	-	V
		Full	2.4	-	-	2.4	-	-	V
Input Leakage Current (Low), I <sub>AL</sub>		25	-	200	-	-	200	-	μА
		Full	-	-	500	-	-	500	μА
Input Leakage Current (High), I <sub>AH</sub>	V <sub>AH</sub> = 4.0V	25	-	20	-	-	20	-	μА
		Full	-	-	40	-	-	40	μА
ANALOG SWITCH CHARACTERISTICS		ı	ı	1	1	1	ı	1	
Analog Signal Range, V <sub>S</sub>		Full	-15	-	+15	-15	-	+15	V
ON Resistance, r <sub>ON</sub>	(Note 2)	25	-	30	50	-	30	50	Ω
		Full	-	-	75	-	-	75	Ω

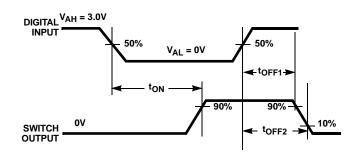
**Electrical Specifications** Supplies = +15V, -15V;  $V_{AH}$  (Logic Level High) = 2.4V,  $V_{AL}$  (Logic Level Low) = +0.8V, GND = 0V, Unless Otherwise Specified **(Continued)** 

	TEST	TEMP		-2		-4, -5, -9			
PARAMETER	CONDITIONS	(°C)	MIN	TYP	MAX	MIN	TYP	MAX	UNITS
r <sub>ON</sub> Match		25	-	3	-	-	3	-	%
OFF Input Leakage Current, I <sub>S(OFF)</sub>		25	-	0.3	10	-	0.3	10	nA
		Full	1	-	100	-	-	50	nA
OFF Output Leakage Current, I <sub>D(OFF)</sub>		25	-	0.3	10	-	0.3	10	nA
		Full	-	-	100	-	-	50	nA
ON Leakage Current, I <sub>D(ON)</sub>		25	ı	0.1	10	-	0.1	10	nA
		Full	-	-	100	-	-	50	nA
POWER SUPPLY CHARACTERISTICS (Note 7)									
Power Dissipation, P <sub>D</sub>		25	-	120	-	-	120	-	mW
		Full	-	-	240	-	-	240	mW
Current, I+ (Pin 13)		25	1	4.5	-	-	4.5	-	mA
		Full	ı	-	10.0	-	-	10.0	mA
Current, I- (Pin 4)		25	1	3.5	-	-	3.5	-	mA
		Full	-	-	6	-	-	6	mA

#### NOTES:

- 2.  $V_{OUT} = \pm 10V$ ,  $I_{OUT} = 1mA$ .
- 3.  $R_L = 1k\Omega$ ,  $C_L = 35pF$ ,  $V_{IN} = +10V$ ,  $V_A = +3V$ . (See Figure 1).
- 4.  $V_A = 3V$ ,  $R_L = 1k\Omega$ ,  $C_L = 10pF$ ,  $V_{IN} = 3V_{RMS}$ , f = 100kHz.
- 5.  $V_A = 3V$ ,  $R_L = 1k\Omega$ ,  $V_{IN} = 3V_{RMS}$ , f = 100kHz.
- 6.  $C_L = 1nF$ ,  $V_{IN} = 0V$ ,  $Q = C_L \times \Delta V_O$ .
- 7.  $V_A = 3V$  or  $V_A = 0$  for all switches.

#### Test Circuits and Waveforms



2V 100mS

TOP: Logic Input (2V/Div.) BOTTOM: Output (5V/Div.) HORIZONTAL: 100ns/Div.

FIGURE 1A. MEASUREMENT POINTS

FIGURE 1B. WAVEFORMS

# Test Circuits and Waveforms (Continued)

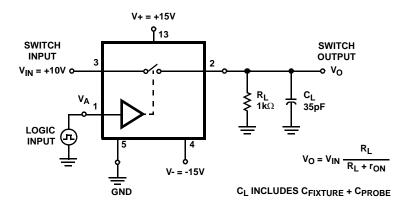
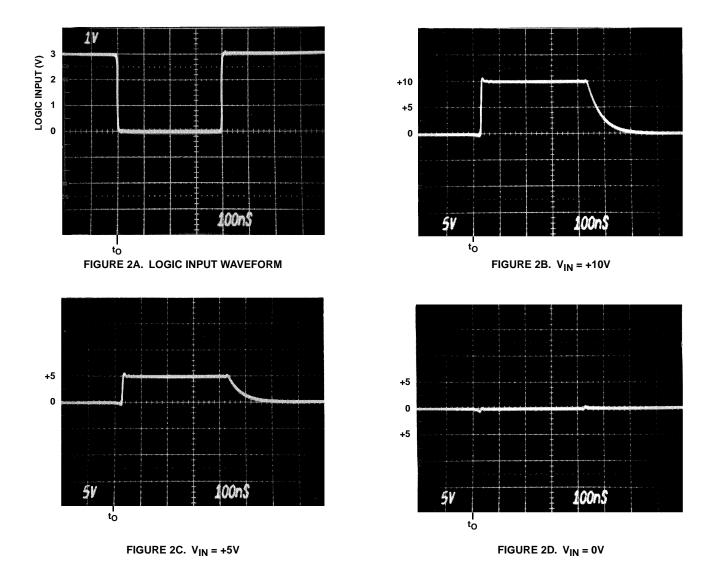
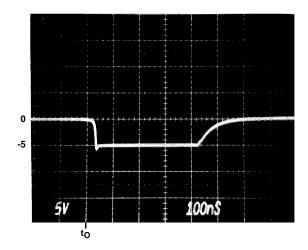


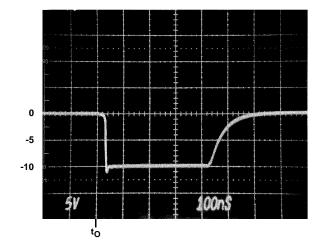
FIGURE 1C. TEST CIRCUIT FIGURE 1. SWITCH  $t_{\mbox{ON}}$  AND  $t_{\mbox{OFF}}$ 



#### Test Circuits and Waveforms (Continued)







# Application Information

#### Logic Compatibility

The HI-201HS is TTL compatible. Its logic inputs (pins 1, 8, 9, and 16) are designed to react to digital inputs which exceed a fixed, internally generated TTL switching threshold. The HI-201HS can also be driven with CMOS logic (0V-15V), although the switch performance with CMOS logic will be inferior to that with TTL logic (0V-5V).

The logic input design of the HI-201HS is largely responsible for its fast switching speed. It is a design which features a unique input stage consisting of complementary vertical PNP and NPN bipolar transistors. This design differs from that of the standard HI-201 product where the logic inputs are MOS transistors.

Although the new logic design enhances the switching speed performance, it also increases the logic input leakage currents. Therefore, the HI-201HS will exhibit larger digital input leakage currents in comparison to the standard HI-201 product.

#### Charge Injection

Charge injection is the charge transferred, through the internal gate-to-channel capacitances, from the digital logic input to the analog output. To optimize charge injection performance for the HI-201HS, it is advisable to provide a TTL logic input with fast rise and fall times.

If the power supplies are reduced from  $\pm 15$ V, charge injection will become increasingly dependent upon the digital input frequency. Increased logic input frequency will result in larger output error due to charge injection.

#### **Power Supply Considerations**

The electrical characteristics specified in this data sheet are guaranteed for power supplies  $V_S = \pm 15 \text{V}$ . Power supply voltages less than  $\pm 15 \text{V}$  will result in reduced switch performance. The following information is intended as a design aid only.

POWER SUPPLY VOLTAGES	SWITCH PERFORMANCE
$\pm 12 \le V_S \le \pm 15V$	Minimal Variation
V <sub>S</sub> < ±12V	Parametric variation becomes increasingly large (increased ON resistance, longer switching times).
V <sub>S</sub> < ±10V	Not Recommended.
V <sub>S</sub> > ±16V	Not Recommended.

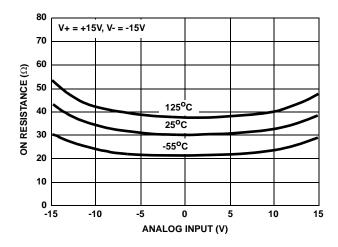
#### Single Supply

The switch operation of the HI-201HS is dependent upon an internally generated switching threshold voltage optimized for  $\pm 15$ V power supplies. The HI-201HS does not provide the necessary internal switching threshold in a single supply system. Therefore, if single supply operation is required, the HI-300 series of switches is recommended. The HI-300 series will remain operational to a minimum +5V single supply.

Switch performance will degrade as power supply voltage is reduced from optimum levels ( $\pm 15V$ ). So it is recommended that a single supply design be thoroughly evaluated to ensure that the switch will meet the requirements of the application.

For further information see Application Notes AN520, AN521, AN531, AN532, AN543 and AN557.

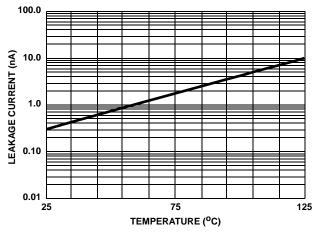
# Typical Performance Curves



80 T<sub>A</sub> = 25°C 70 V+ = +8V, V- = -8V +10V, V- = -10V 60 ON RESISTANCE (\(\O\)) 50 40 30 20 V+ = +15V, V- = -15V 10 0 -10 10 -15 0 5 15 ANALOG INPUT (V)

FIGURE 3. ON RESISTANCE vs ANALOG SIGNAL LEVEL

FIGURE 4. ON RESISTANCE vs ANALOG SIGNAL LEVEL



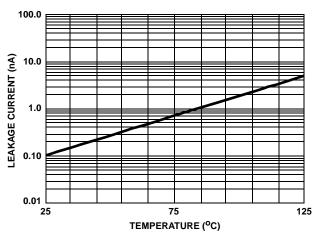
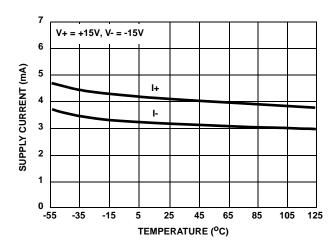


FIGURE 5.  $I_{S(OFF)}$  OR  $I_{D(OFF)}$  vs TEMPERATURE  $\dagger$ 

FIGURE 6.  $I_{D(ON)}$  vs TEMPERATURE †

<sup>†</sup> Theoretically, leakage current will continue to decrease below 25°C. But due to environmental conditions, leakage measurements below this temperature are not representative of actual switch performance.



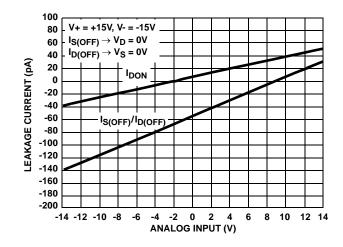
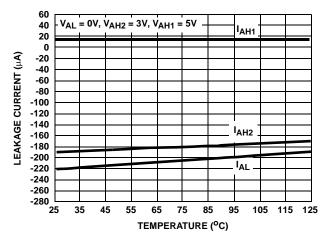


FIGURE 7. SUPPLY CURRENT vs TEMPERATURE

FIGURE 8. LEAKAGE CURRENT vs ANALOG INPUT VOLTAGE

## Typical Performance Curves (Continued)

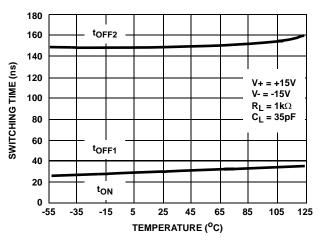


10 V+ = +15V, V- = -15V, T<sub>A</sub> = 25°C | Is(OFF) → V<sub>D</sub> = 0V | ID(OFF) → V<sub>S</sub> = 0V | ID(O

FIGURE 9. DIGITAL INPUT LEAKAGE CURRENT vs TEMPERATURE †

FIGURE 10. LEAKAGE CURRENT vs ANALOG INPUT VOLTAGE

† Theoretically, leakage current will continue to decrease below 25°C. But due to environmental conditions, leakage measurements below this temperature are not representative of actual switch performance.



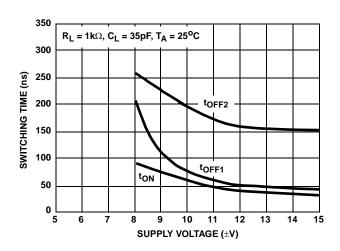
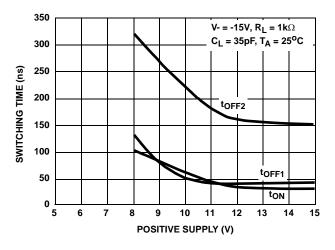


FIGURE 11. SWITCHING TIME vs TEMPERATURE





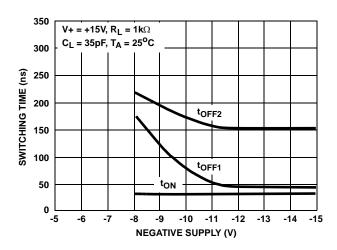


FIGURE 13. SWITCHING TIME vs POSITIVE SUPPLY VOLTAGE

FIGURE 14. SWITCHING TIME vs NEGATIVE SUPPLY VOLTAGE

## Typical Performance Curves (Continued)

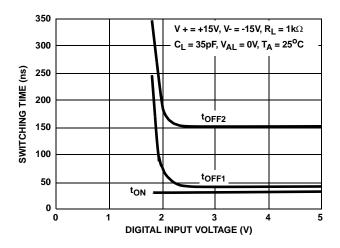


FIGURE 15. SWITCHING TIME vs INPUT LOGIC VOLTAGE

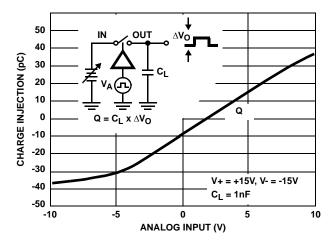


FIGURE 17. CHARGE INJECTION vs ANALOG VOLTAGE

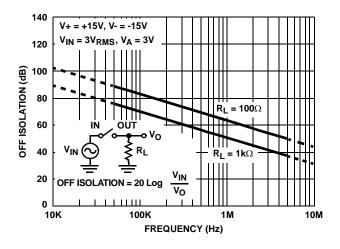


FIGURE 19. OFF ISOLATION vs FREQUENCY

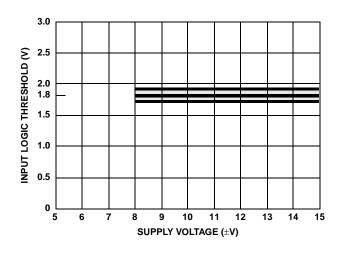


FIGURE 16. INPUT SWITCHING THRESHOLD vs SUPPLY VOLTAGE

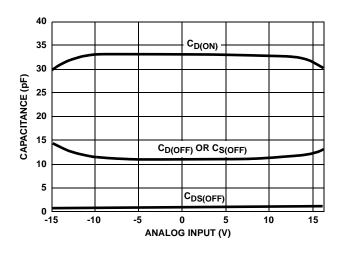


FIGURE 18. CAPACITANCE vs ANALOG VOLTAGE

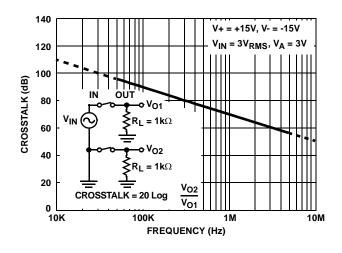


FIGURE 20. CROSSTALK vs FREQUENCY

#### Die Characteristics

#### **DIE DIMENSIONS**

2440µm x 2860µm x 485µm

#### **METALLIZATION**

Type: CuAl

Thickness: 16kÅ ±2kÅ

#### **PASSIVATION**

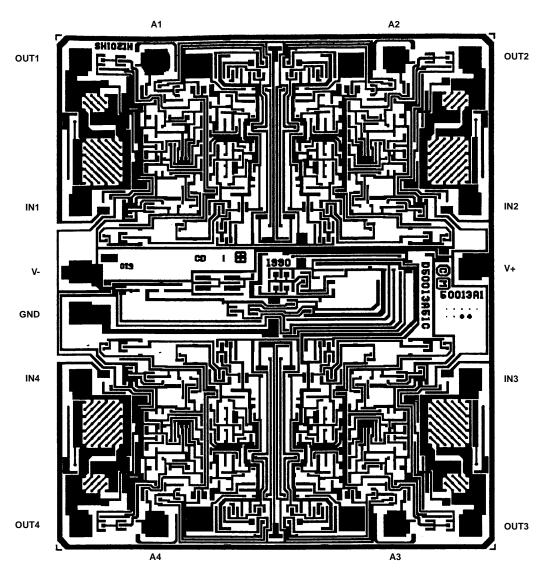
Type: Nitride Over Silox Nitride Thickness: 3.5kÅ ±1kÅ Silox Thickness: 12kÅ ±2kÅ

#### **WORST CASE CURRENT DENSITY**

 $9.5 \times 10^4 \text{ A/cm}^2$ 

## Metallization Mask Layout

HI-201HS



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